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Correction: Effects of pressure and temperature on topological electronic materials X_2Y_3 ($X = \text{As}, \text{Sb}, \text{Bi}$; $Y = \text{Se}, \text{Te}$) using first-principles

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Correction for 'Effects of pressure and temperature on topological electronic materials X_2Y_3 ($X = \text{As}, \text{Sb}, \text{Bi}$; $Y = \text{Se}, \text{Te}$) using first-principles' by Le Fang et al., *Phys. Chem. Chem. Phys.*, 2023, **25**, 20969–20978, <https://doi.org/10.1039/D3CP01951A>.

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The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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